## Spin transport through a single self-assem bled InAs quantum dot with ferrom agnetic leads

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W e have fabricated a lateral double barrier magnetic tunnel junction (M T J) which consists of a single self-assembled InAs quantum dot (Q D) with ferrom agnetic C o leads. The M T J shows clear hysteretic tunnel magnetoresistance (TM R) e ect, which is evidence for spin transport through a single sem iconductor Q D. The TM R ratio and the curve shapes are varied by changing the gate voltage.

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The research eld of sem iconductor-based spin electronics (spintronics) has opened up a new technology for spin manipulation by means other than magnetic

eld.1, 2] For developing sem iconductor nanospintronic applications and discovering novel physical phenom ena, one is extremely interested in technological possibilities for spin injection into a single sem iconductor quantum dot (QD) which behaves as an arti cialatom .3] To date, m any theoretical studies of spin transport through a single nonmagnetic island with ferrom agnetic leads have been reported, [4, 5, 6, 7, 8, 9] and spin accumulation in the island was predicted in their reports. Very recently, form etallic systems, spin in jection into a single nonm agnetic nanoparticle was achieved, [10] which indicates the occurrence of spin accumulation. For an individual carbon nanotube (CNT) with ferrom agnetic leads, the spin transport [11, 12] and its gate-control [13, 14, 15, 16] have also been dem onstrated, show ing possible spintronic applications using CNTs. However, no experim ental work on spin-dependent transport through a single sem iconductor QD has been reported yet.

Recently, Jung et al.[17] succeeded in transport m easurements for a single self-assembled InAsQD in contact with nonmagnetic leads and clearly observed shell structures due to an articical atom ic nature. Replacing the nonmagnetic leads with ferrom agnetic ones, we can inject spin-polarized electrons from the ferrom agnetic leads into a single InAs QD. A number of works proposed that if the spin relaxation time in the QD is su ciently long, spin accumulation can occur, which is detected through tunneling magnetoresistance (TMR) e ects.4, 5, 6, 7, 8, 9, 18, 19] In sem iconductor heterostructures, the electrical detection of the spin accumulation in the double barrier magnetic tunnel junction (MTJ), (G a,M n)As/A IAs/G aAs/A IAs/(G a,M n)As, has been demonstrated by measuring the TMR e ect.[8]

In this letter, we report on the observation of spin transport through a single sem iconductor QD using a lateral double barrier MTJ composed of ferrom agnetic C o leads and a single self-assem bled InAsQD.TheMTJ shows clear C oulom b blockade e ects and the TMR effects. The TMR features are varied evidently by changing the gate voltage, meaning that the spin transport can be tuned by applying the electric eld.

Self-assem bled InAs QDs were grown on a substrate made of, from the top, 200-nm-thick GaAs bu er layer, 120-nm-thick AlGaAs insulating layer, and  $n^+ - GaAs(001)$ . The  $n^+ - GaAs(001)$  was used as a backgate electrode. Using electron-beam lithography and lift-o m ethod, we fabricated the wire-shape Co leads with a

30-nm gap. Our device structure is a lateral M TJ, schem atically illustrated in Fig.1 (a). A single InAsQD is in contact with two Co wires that have a thickness of 40 nm, deposited by means of an ultrahigh vacuum evaporator with a base pressure of 1  $10^9$  Torr. In order to induce asymmetric shape anisotropy, one of the Co leads was formed to be 1 m-wide and 20 m-long,

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FIG.1: (a) Schem atic diagram of a Co/InA s/Co double barrier magnetic tunnel junction. (b) Scanning electron micrograph of the Co/InA s/Co junction structure used in the present study. The inset shows an enlarged micrograph in the enclosed area.

while the other was form ed to be 200 nm -wide and 20 m -long, giving rise to di erent switching elds for each lead. Since there exists a natural oxide layer form ed on the InAs surface, [20] the Co/InAs interface layers act as tunnel barriers. Thus, the device used in this study is a lateral double barrier M TJ, Co/InAs/Co. A scanning electron m icrograph of the Co/InAs/Co M TJ is shown in Fig. 1 (b). A single InAsQD with a size of 80 nm is located between the two Co leads. Transport m easurem ents were perform ed by the dc m ethod in a  ${}^{3}\text{He}$   ${}^{4}\text{He}$  dilution refrigerator at 50 m K.

The current vs source-drain voltage (I  $~\rm V_{SD}$ ) characteristics of the Co/InA s/CoMTJ at 50 mK are shown in Fig. 2(a) for various backgate voltages (V $_{\rm G}$ ). These curves are measured under an external magnetic eld of

0.2 T parallel to the long axis of the Co leads, where the magnetizations of both leads become nearly parallel. The I V\_{SD} characteristics clearly show the zero conductance in the vicinity of V\_{SD} = 0 V, indicating C oulom b blockade. Also, step-like I V\_{SD} structures, so-called C oulom b staircase, can be seen. It should be noted that the resistance jumps of G are much larger than the quantum resistance of h/e<sup>2</sup> 25.8 k, and the junction resistance is very large com pared to the previous studies by Jung et al.[17] who used nonm agnetic A u leads. Thus, the couplings of the dot to the C o leads are very weak and sequential tunneling processes are likely to



FIG. 2: (a) Current-voltage (I  $\,$  V\_{SD}) characteristics of a Co/InA s/Co junction structure, measured at 50 mK, for various backgate voltages, V\_G. (b) D i erential conductance, dI/dV\_{SD}, as functions of V\_{SD} and V\_G. (c) M agnetic eld dependence of tunnel resistance for various V\_{SD}. The inset shows schem atic illustrations of the magnetic con guration of the leads.

be dom inant for our sam ple. Furtherm ore, the I  $\rm V_{SD}$  curves show asymmetric features about the polarity of  $\rm V_{SD}$ . This means that in our device the two tunnel barriers is asymmetric. In Fig. 2 (b) we also measure the di erential conductance, dI/dV\_{SD}, as functions of V\_{SD} and V\_G. Unfortunately, since the accessible range of the V\_G is very narrow, we observe only one diam ond-like shape of the dI/dV\_{SD} in Fig. 2 (b). However, these operations verify that our device is working as a single electron transistor, as well as nonm agnetic Au leads.[17] W e also emphasize that this is the demonstration of C oulom b blockade e ects for a single sem iconductor QD with ferrom agnetic leads.

Figure 2 (c) shows the magnetic eld dependence of the tunnel resistance for  $V_{SD} = 22.5, 32.5, \text{ and } 41 \text{ mV}$  at  $V_{G}$ = 200 mV, measured at 50 mK. The magnetic eld (H) is applied parallel to the long axis of the wires. The data traces are recorded for two sweep directions of the magnetic eld: the blue curves are up-sweep from 0.2 to +0.2 T, while the red curves are dow n-sweep from + 0.2to 02T.Here, the TMR ratio (%) is de ned as f (H  $I_{0:1T}$  )/ $I_{0:1T}$  g 100, where  $I_{H}$  and  $I_{0:1T}$  are the tunnel currents for magnetic eld of H and for H = 0.1 T, respectively. First, we focus on the data for  $V_{SD}$  = 41 m V.W hen the magnetic eld is swept from + 0.2 T toward negative elds (red curve), the magnetizations of the two Co leads are changed from a parallel con guration into an approximately anti-parallel con guration, as



FIG. 3: (a) Tunneling magnetoresistance curves of a Co/InAs/Co junction measured at  $V_{SD} = 41 \text{ mV}$  at 50 mK for (a)  $V_G = 600 \text{ mV}$ , (b) 400 mV, (c) 200 mV, (d) 100 mV, (e) 50 mV, and (f) 0 mV.

shown in the inset of Fig. 2 (c), and the tunnel resistance becomes large at H 0.02 T. Similar features are seen in up-sweep procedure (blue curve). This behavior is a positive TMR e ect. The TMR curve having typical hysteretic features is also observed for  $V_{\rm SD} = 32.5$  mV. These TMR curves clearly suggest that electron spins are conserved in the tunneling transport processes. These are the observation of spin-dependent transport through a single sem iconductor QD with ferrom agnetic leads. On the other hand, the TMR signal can not be clearly seen at  $V_{\rm SD} = 22.5$  mV. For our device the spin transport is detected only at higher  $V_{\rm SD}$  regime, and it is di cult to discuss the detailed correlation between I  $V_{\rm SD}$  characteristics and TMR features.

In Figs. 3(a)-(f), we show the TMR curves for various V<sub>G</sub> measured at V<sub>SD</sub> =  $41 \text{ mV} \cdot \text{W}$  e note that the magnitude of the TMR ratio and the curve shape can

be manipulated by changing V<sub>G</sub>. From V<sub>G</sub> = 600 to 100 mV [Figs. 3(a)-(d)], the change in the TMR ratio is smallbut slight variation in the shape of the TMR curve is seen with decreasing V<sub>G</sub>. These features are reproduced qualitatively. Surprisingly, the shape of the TMR curve and the TMR ratio change markedly at V<sub>G</sub> = 50 and 0 mV [Figs. 3(e) and 3(f)].

One of the possible mechanism sof the spin-dependent transport presented here is spin accumulation in a single InAsQD by injecting spin-polarized electrons from one ferrom agnetic C o lead. [4, 5, 6, 7, 8, 9, 18, 19] In theoreticalstudies based on the spin accum ulation, [4, 5, 6, 7, 8, 9] the bias dependence and the gate-voltage dependence of the TMR ratio have been predicted. By means of optical measurements, the spin relaxation time in self-assembled InAsQDs was deduced to be 1 ns at low tem perature, [21] which is long enough to induce a nonequilibrium spin accumulation. However, the unexpected large TMR ratio, shown in Figs. 3(e) and 3(f), can not currently be explained by previously reported theoretical predictions. [4, 5, 6, 7, 8] A lso, the origin of the shape change in the TMR curve is unclear yet. In this regard, we speculate that the in uence of com plicated dom ain structures in the wider lead and/or the magneto-Coulomb e ect22] on the tunnel conductance should also be taken into account.

Recently, for PdN i/CNT /PdN i system s,[13] the gatedependent TMR was reported, in which the dependence may originate from the discrete energy level depending on the gate voltage and the spin orientation of the ferromagnetic leads. In our case, the in uence of the discrete levels in the QD, which may have the spin splitting due to spin accumulation, [4, 5, 6, 7, 8, 9] should also be considered.

In sum m ary, we have fabricated a double barrier M T J which consists of a single self-assem bled  $InA \otimes QD$  in contact with ferrom agnetic C o leads. C lear C oulom b block-ade e ects and TM R e ects are demonstrated and they can be varied by changing the gate bias voltage.

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